

100V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	Max R _{DS(on)}	Max I _D T _A = +25°C (Note 6)
100V	$230 \text{m}\Omega @ V_{GS} = 10V$	1.9A
100 V	$300 \text{m}\Omega$ @ $V_{GS} = 4.5 \text{V}$	1.68A

Description and Applications

This MOSFET utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes it ideal for high-efficiency, low voltage, power management applications.

- DC DC Converters
- Power Management Functions
- **Disconnect Switches**
- Motor Control

Features and Benefits

- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- SOT26 Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

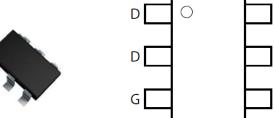
Mechanical Data

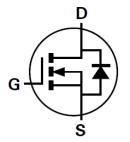
Case: SOT26

D

- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.015 grams (Approximate)







Top View

Pinout Top-view

Device Symbol

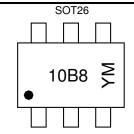
Ordering Information (Note 4)

Part Number	Reel Size (inch)	Tape Width (mm)	Quantity Per Reel
ZXMN10B08E6TA	7	8	3,000
ZXMN10B08E6TC	13	8	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



10B8 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: C = 2015) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Date Code Ney								
Year	2015	2016	2017	2018	2019	2020	2021	2022
Code	С	D	E	F	G	Н		J

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Chara	acteristic		Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	100	V
Gate-Source Voltage			V _{GSS}	±20	V
		(Note 6)	lο	1.9	
Continuous Drain Current	$V_{GS} = 10V$	$T_A = +70^{\circ}C \text{ (Note 6)}$		1.5	Α
		(Note 5)		1.6	
Pulsed Drain Current		(Note 7)	I _{DM}	9	Α
Continuous Source Current (Body	(Note 6)	I _S	2.5	Α	
Pulsed Source Current (Body Diode) (Note 7)			I _{SM}	9	Α

Thermal Characteristics (@TA = +25 °C, unless otherwise specified.)

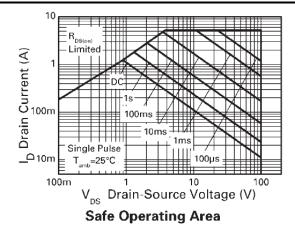
Characteristic		Symbol	Value	Unit
Power Dissipation	(Note F)	D	1.1	W
Linear Derating Factor	(Note 5)	P_D	8.8	mW/°C
Power Dissipation	(Nata C)	В	1.7	W
near Derating Factor (Note 6)		P _D	13.6	mW/°C
Thermal Desistance Junction to Ambient	(Note 5)		113	0000
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	73	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

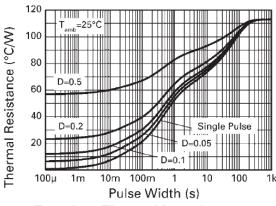
Notes:

- 5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- 6. For a device surface mounted on FR4 PCB measured at t ≤ 5 secs.

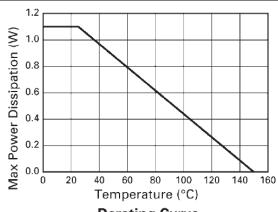
 7. Repetitive rating 25mm x 25mm FR4 PCB, D = 0.02, pulse width 300μs pulse width limited by maximum junction temperature. Refer to Transient

Thermal Characteristics

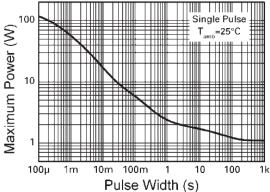




Transient Thermal Impedance









Electrical Characteristics (@T_A = +25 °C, unless otherwise specified.)

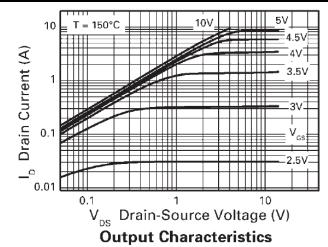
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS				•	•		
Drain-Source Breakdown Voltage	BV _{DSS}	100	_	_	V	$I_D = 250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	0.5	μΑ	$V_{DS} = 100V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(th)}	1.0		3.0	V	$I_D=250\mu A,\ V_{DS}=V_{GS}$	
				0.23		V _{GS} = 10V, I _D = 1.6A	
Static Drain-Source On-Resistance (Note 8)	R _{DS(ON)}	_	_	0.30	Ω	$V_{GS} = 4.5V, I_D = 1.4A$	
				0.50		$V_{GS} = 4.3V, I_D = 1.1A$	
Forward Transconductance (Notes 8 & 10)	g fs		4.8	_	S	V _{DS} = 15V, I _D = 1.6A	
Diode Forward Voltage (Note 8)	V_{SD}	_	0.85	0.95	V	$T_J = +25$ °C, $I_S = 2.0$ A, $V_{GS} = 0$ V	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	_	497	_	pF	V 50V V 6V	
Output Capacitance	Coss	_	29	_	pF	$V_{DS} = 50V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	18	_	pF	1 - 1.01/11/2	
Gate Charge (Note 9)	Qg	_	5.0	_	nC	$V_{DS} = 50V$, $V_{GS} = 5V$, $I_{D} = 1.6A$	
Total Gate Charge (Note 9)	Qg	_	9.2	_	nC		
Gate-Source Charge (Note 9)	Q _{gs}	_	1.7	_	nC	$V_{DS} = 50V, V_{GS} = 10V,$ $I_{D} = 1.6A$	
Gate-Drain Charge (Note 9)	Q _{gd}	_	2.5	_	nC	-ID = 1.6A	
Turn-On Delay Time (Note 9)	t _{d(on)}	_	2.9	_	ns		
Turn-On Rise Time (Note 9)	t _r	_	2.1	_	ns	$V_{DD} = 50V, I_D = 1.0A,$	
Turn-Off Delay Time (Note 9)	t _{d(off)}	_	12.1	_	ns	$R_G \cong 6.0\Omega$, $V_{GS} = 10V$	
Turn-Off Fall Time (Note 9)	t _f	_	5.0	_	ns]	
Reverse Recovery Time	t _{rr}	_	32	_	ns	T _J = +25°C, I _F = 1.7A,	
Reverse Recovery Charge	Q _{rr}	_	40		nC	di/dt = 100A/μs	

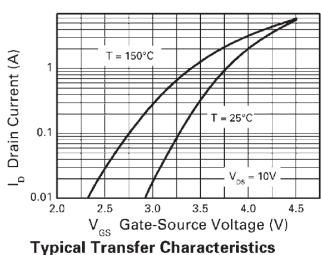
Notes:

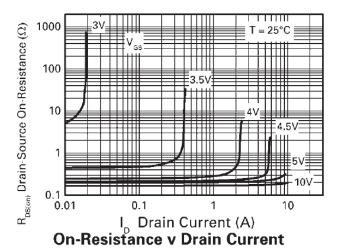
^{8.} Measured under pulsed conditions. Width \leq 300 µs. Duty cycle \leq 2%. 9. Switching characteristics are independent of operating junction temperature. 10. For design aid only, not subject to production testing.

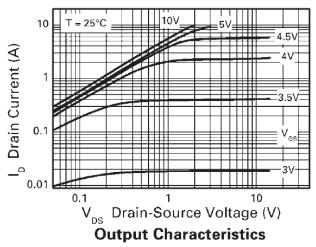


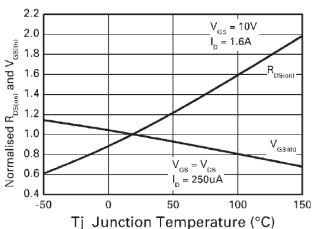
Typical Characteristics



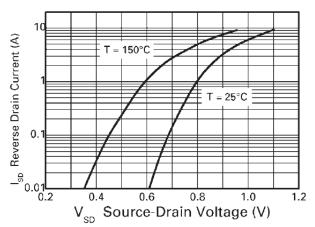








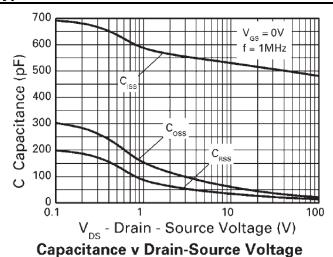
Normalised Curves v Temperature

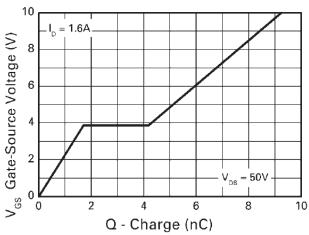


Source-Drain Diode Forward Voltage



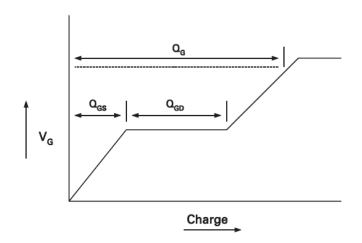
Typical Characteristics (continued)

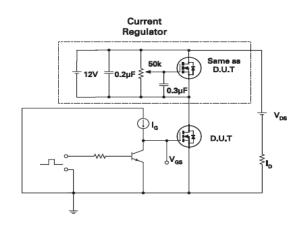




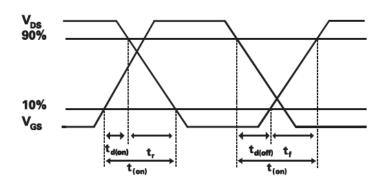
Gate-Source Voltage v Gate Charge

Test Circuits

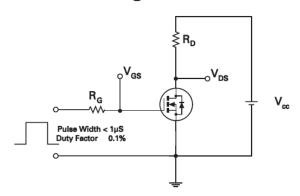




Basic Gate Charge Waveform



Gate Charge Test Circuit



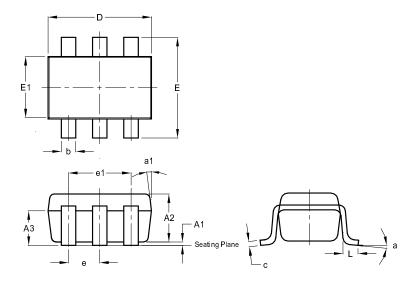
Switching Time Waveforms

Switching Time Test Circuit



Package Outline Dimensions

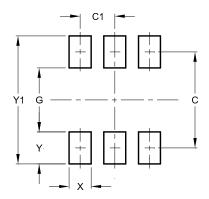
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT26						
Dim	Min	Max	Тур				
A1	0.013	0.10	0.05				
A2	1.00	1.30	1.10				
A3	0.70	0.80	0.75				
b	0.35	0.50	0.38				
С	0.10	0.20	0.15				
D	2.90	3.10	3.00				
е	1	1	0.95				
e1	-	1	1.90				
Е	2.70	3.00	2.80				
E1	1.50	1.70	1.60				
L	0.35	0.55	0.40				
а	а -		8°				
a1	-	-	7°				
All	Dimen	sions	in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
Х	0.55
Υ	0.80
Y1	3.20



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